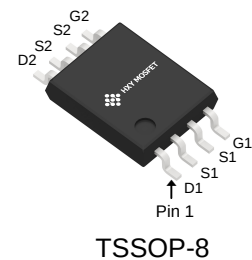




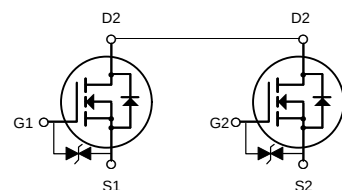
General Description

The DMN2016UTS-13 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent R_{DS(on)} and gate charge for most of the small power switching and load switch applications. The meet the RoHS and Product requirement with full function reliability approved.



General Features

$V_{DS} = 20V$ $I_D = 7.5A$
 $R_{DS(ON)} < 13m\Omega$ @ $V_{GS}=4.5V$
 $R_{DS(ON)} < 16m\Omega$ @ $V_{GS}=2.5V$



Dual N-Channel MOSFET

Application

Battery protection
Load switch
Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMN2016UTS-13	TSSOP-8	HXY MOSFET	5000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 10	V
I_D	Drain Current-Continuous	7.5	A
I_{DM}	Drain Current-Pulsed (Note 1)	24	A
P_D	Maximum Power Dissipation	1.25	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	111	°C/W



Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.7	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=4.5A$	-	11.5	13	m Ω
		$V_{GS}=2.5V, I_D=3.5A$	-	14	16	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=3.5A$	-	20	-	S
Input Capacitance	C_{iss}	$V_{DS}=8V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	955	-	PF
Output Capacitance	C_{oss}		-	200	-	PF
Reverse Transfer Capacitance	C_{rss}		-	150	-	PF
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=3.5A$ $V_{GS}=4.5V, R_{GEN}=6\Omega$	-	8	-	nS
Turn-on Rise Time	t_r		-	17	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	27	-	nS
Turn-Off Fall Time	t_f		-	8.8	-	nS
Total Gate Charge	Q_g	$V_{DS}=10V, I_D=7A,$ $V_{GS}=4.5V$	-	11.3	-	nC
Gate-Source Charge	Q_{gs}		-	1.89	-	nC
Gate-Drain Charge	Q_{gd}		-	3.56	-	nC
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=1.7A$	-	0.75	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



Typical Characteristics

Figure1: Output Characteristics

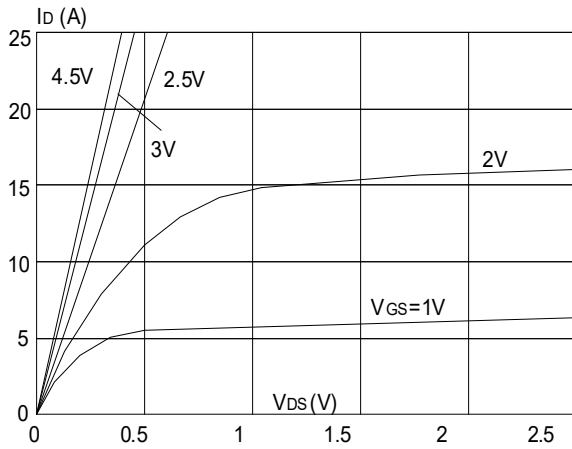


Figure 2: Typical Transfer Characteristics

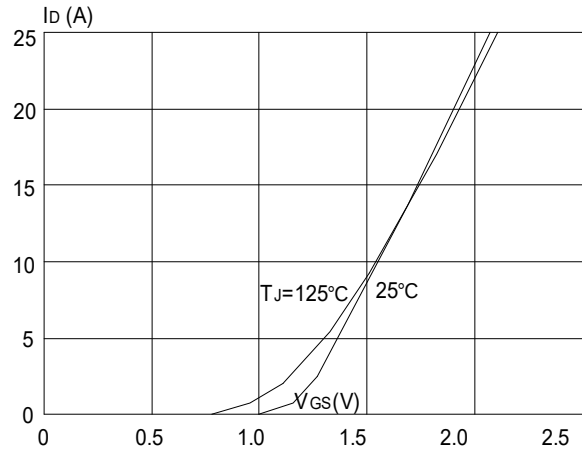


Figure 3: On-resistance vs. Drain Current

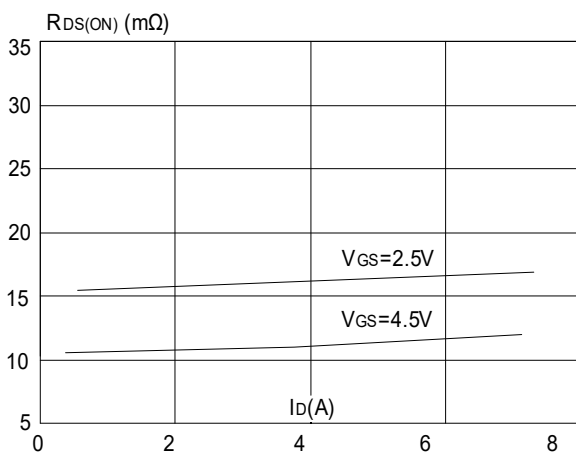


Figure 4: Body Diode Characteristics

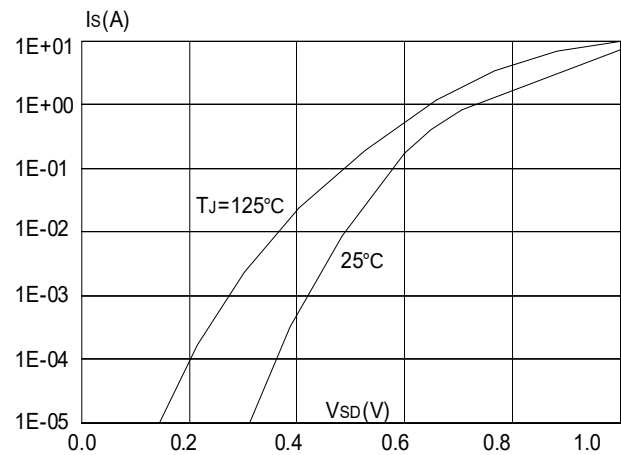


Figure 5: Gate Charge Characteristics

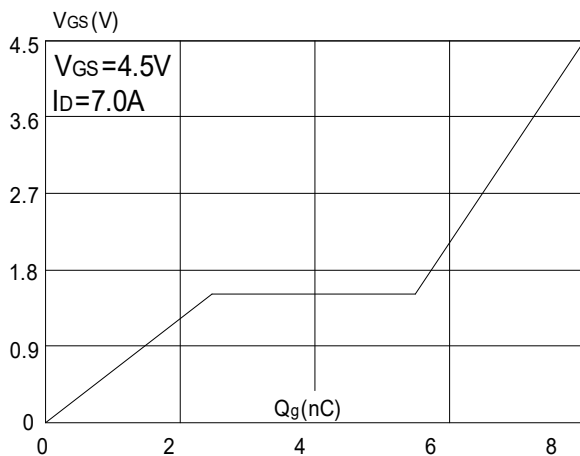


Figure 6: Capacitance Characteristics

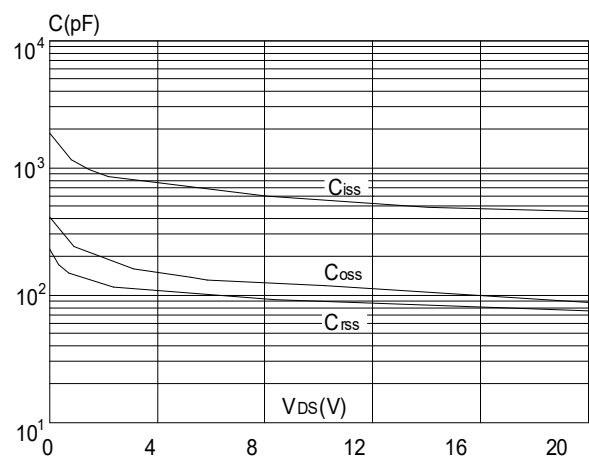




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

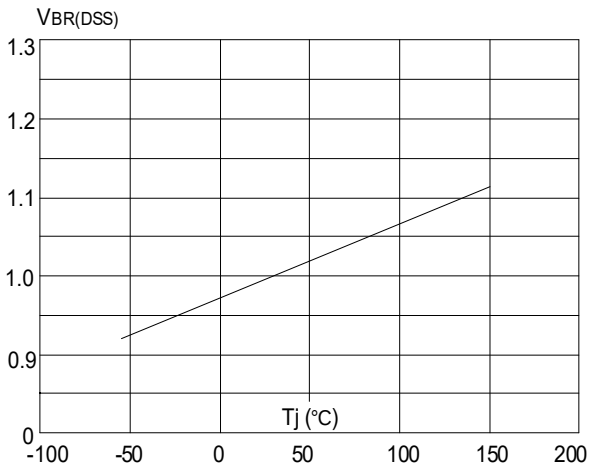


Figure 8: Normalized on Resistance vs. Junction Temperature

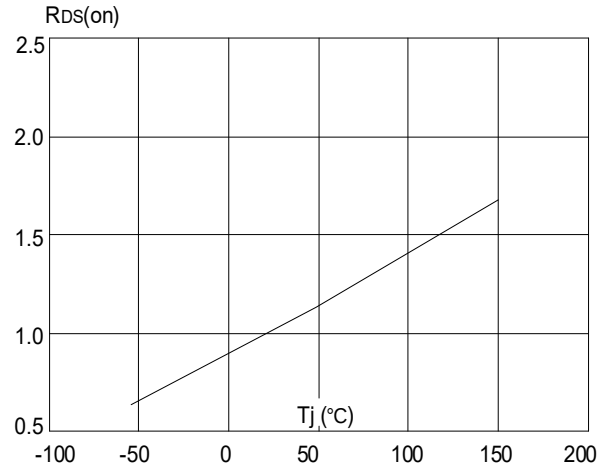


Figure 9: Maximum Safe Operating Area

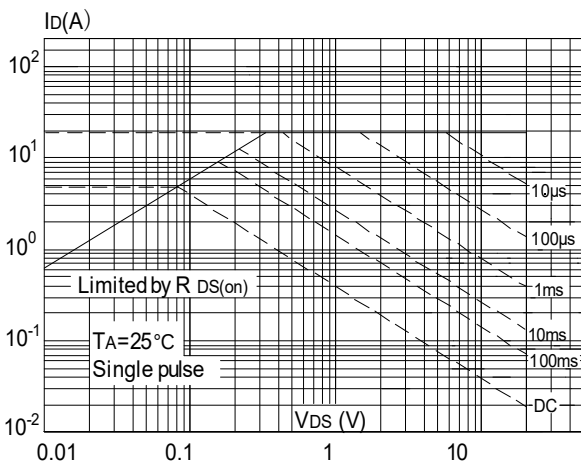


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

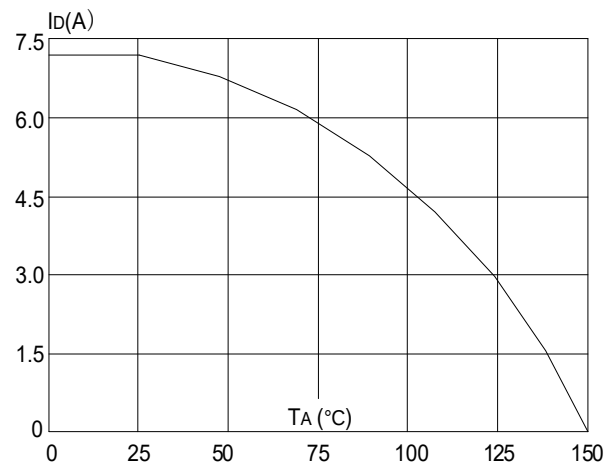
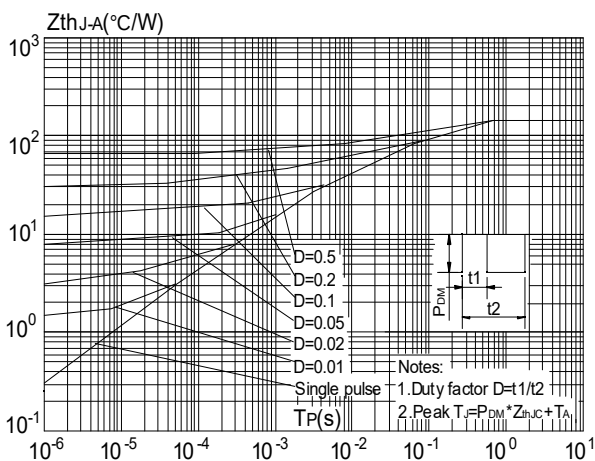
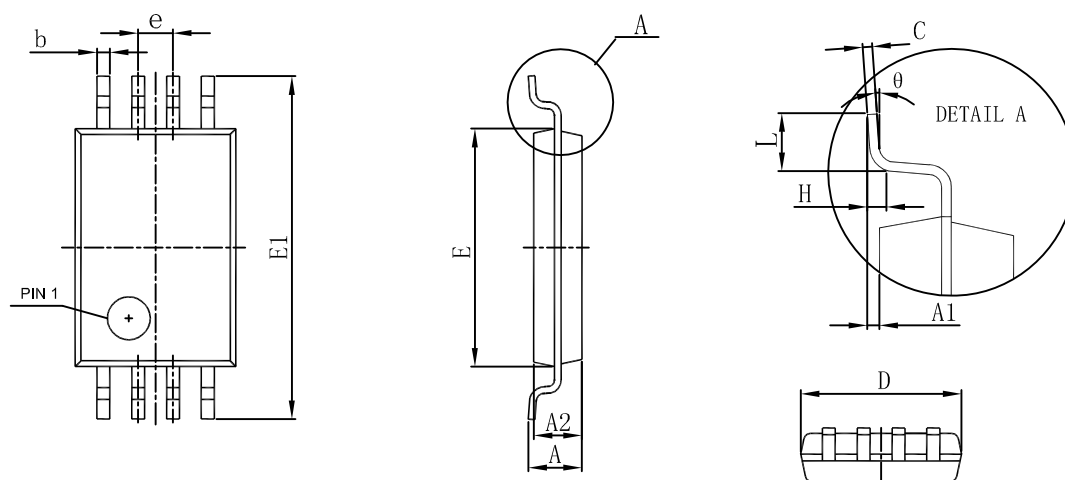


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





TSSOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.200		0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°



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